## An effect of electric field on a cone angle at an easy-cone state in CoFeB/MgO stack investigated by ferromagnetic resonance

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Magnetization reversal by spin-transfer torque (STT) is of importance for non-volatile memory applications using magnetic tunnel junctions. Recently, the free layer with an easy-cone state, which can be obtained when the first- and second-order magnetic anisotropy energy constants satisfy a certain condition, is attracting much attention for improving the STT-induced reversal efficiency [1-2]. In this study, we investigate an effect of the electric field E on the cone angle at the easy-cone state in Ta/CoFeB/ MgO system using ferromagnetic resonance (FMR) to elucidate the variation in the intrinsic critical current under application of voltage.

Stack, from substrate side, Ta (5 nm)/ Ru (10 nm)/ Ta (5 nm)/ Co<sub>0.2</sub>Fe<sub>0.6</sub>B<sub>0.2</sub> (1.6 nm)/ MgO (2 nm)/ Al<sub>2</sub>O<sub>3</sub> (5 nm) is deposited on thermally oxidized Si substrate by sputtering, followed by annealing at 300°C for 1 h under perpendicular magnetic field of 0.4 T. The stack is processed into 1 mm $\phi$  circular mesa. Insulator Al<sub>2</sub>O<sub>3</sub> (32 nm) is deposited by atomic layer deposition to cover the device, and top electrode Cr (3 nm) /Au (50 nm) are formed by evaporation and lift-off technique.

We evaluate anisotropy fields  $H_{K1}^{\text{eff}}$  and  $H_{K2}$  by FMR using TE<sub>011</sub> cavity with 9 GHz microwave at temperature *T* varied from 4 K to 300 K [3]. We first study temperature dependence of  $H_{K1}^{\text{eff}}$  and  $H_{K2}$  in an absence of electric field. Both  $H_{K1}^{\text{eff}}$  and  $H_{K2}$  increase with decreasing temperature. As a result, below 200 K, the easy-cone state is observed. We then study the electric field dependence of  $H_{K1}^{\text{eff}}$  and  $H_{K2}$  as a function of *T*. At all the measured *T*,  $H_{K1}^{\text{eff}}$  varies by application of *E* while  $H_{K2}$  is virtually constant, which is consistent with previous reports [3,4]. Due to the difference in the dependence of anisotropy field on electric field, the cone angle is modulated by *E* (~10 degrees with *E* = 0.1 V/nm), which manifests itself in the magnetic field angle dependence of resonance field as a function of *E*. The present result indicates that the intrinsic critical current with the easy-cone state is modulated by the electric field through variation of the cone angle.

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- [1] R. Matsumoto et al., Appl. Phys. Express 8, 063007 (2015).
- [2] A. A. Timopheev et al., Sci. Rep. 6, 26877 (2016).
- [3] A. Okada et al., Appl. Phys. Lett. 105, 052415 (2014).
- [4] S. Kanai et al., Appl. Phys. Lett. 105, 242409 (2014).